

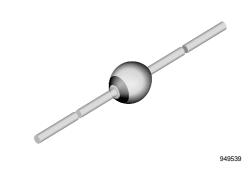
# BYT53.

### **Vishay Semiconductors**

## **Ultra Fast Avalanche Sinterglass Diode**

#### Features

- Glass passivated junction
- Hermetically sealed package
- Low reverse current
- Soft recovery characteristics
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



#### **Applications**

Very fast rectification and switches Switched mode power supplies High-frequency inverter circuits

#### **Mechanical Data**

Case: SOD-57 Sintered glass case Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: approx. 369 mg

#### Parts Table

| Part   | Type differentiation                             | Package |
|--------|--|---------|
| BYT53A | V <sub>R</sub> = 50 V; I <sub>FAV</sub> = 1.9 A  | SOD-57  |
| BYT53B | V <sub>R</sub> = 100 V; I <sub>FAV</sub> = 1.9 A | SOD-57  |
| BYT53C | V <sub>R</sub> = 150 V; I <sub>FAV</sub> = 1.9 A | SOD-57  |
| BYT53D | V <sub>R</sub> = 200 V; I <sub>FAV</sub> = 1.9 A | SOD-57  |
| BYT53F | V <sub>R</sub> = 300 V; I <sub>FAV</sub> = 1.9 A | SOD-57  |
| BYT53G | V <sub>R</sub> = 400 V; I <sub>FAV</sub> = 1.9 A | SOD-57  |

#### **Absolute Maximum Ratings**

T<sub>amb</sub> = 25 °C, unless otherwise specified

| Parameter  | Test condition                        | Part   | Symbol                            | Value | Unit |
|--|---------------------------------------|--------|-----------------------------------|-------|------|
| Reverse voltage = Repetitive<br>peak reverse voltage | see electrical characteristics        | BYT53A | V <sub>R</sub> = V <sub>RRM</sub> | 50    | V    |
|  |                                       | BYT53B | $V_{R} = V_{RRM}$                 | 100   | V    |
|  |                                       | BYT53C | $V_{R} = V_{RRM}$                 | 150   | V    |
|  |                                       | BYT53D | $V_{R} = V_{RRM}$                 | 200   | V    |
|  |                                       | BYT53F | $V_{R} = V_{RRM}$                 | 300   | V    |
|  |                                       | BYT53G | $V_{R} = V_{RRM}$                 | 400   | V    |
| Peak forward surge current                           | t <sub>p</sub> = 10 ms, half sinewave |        | I <sub>FSM</sub>                  | 50    | А    |





| Parameter                               | Test condition                    | Part | Symbol           | Value         | Unit |
|---|-----------------------------------|------|------------------|---------------|------|
| Average forward current                 | l = 10 mm, T <sub>L</sub> = 25 °C |      | I <sub>FAV</sub> | 1.9           | А    |
| Junction and storage temperature range  |                                   |      | $T_j = T_{stg}$  | - 55 to + 175 | °C   |
| Non repetitive reverse avalanche energy | I <sub>(BR)R</sub> = 1 A          |      | E <sub>R</sub>   | 20            | mJ   |

## **Maximum Thermal Resistance**

 $T_{amb}$  = 25 °C, unless otherwise specified

| Parameter        | Test condition                             | Part | Symbol            | Value | Unit |
|------------------|--|------|-------------------|-------|------|
| Junction ambient | $I = 10 \text{ mm}, T_L = \text{constant}$ |      | R <sub>thJA</sub> | 45    | K/W  |
|                  | on PC board with spacing<br>25 mm          |      | R <sub>thJA</sub> | 100   | K/W  |

### **Electrical Characteristics**

T<sub>amb</sub> = 25 °C, unless otherwise specified

| Parameter             | Test condition  | Part | Symbol          | Min | Тур. | Max | Unit |
|-----------------------|---|------|-----------------|-----|------|-----|------|
| Forward voltage       | I <sub>F</sub> = 1 A  |      | V <sub>F</sub>  |     |      | 1.1 | V    |
|                       | I <sub>F</sub> = 1 A, T <sub>j</sub> = 175 °C                         |      | V <sub>F</sub>  |     |      | 0.9 | V    |
| Reverse current       | $V_{R} = V_{RRM}$   |      | I <sub>R</sub>  |     |      | 5   | μA   |
|                       | $V_{R} = V_{RRM}, T_{j} = 150 \ ^{\circ}C$                            |      | I <sub>R</sub>  |     |      | 200 | μA   |
| Reverse recovery time | I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, i <sub>R</sub> = 0.25 A |      | t <sub>rr</sub> |     |      | 50  | ns   |

## Typical Characteristics (Tamb = 25 °C unless otherwise specified)

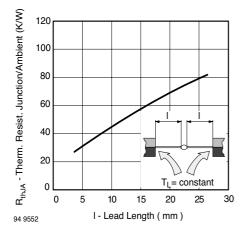


Figure 1. Max. Thermal Resistance vs. Lead Length

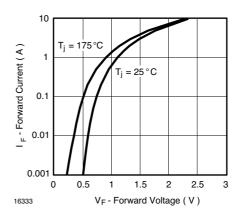


Figure 2. Forward Current vs. Forward Voltage



BYT53. Vishay Semiconductors

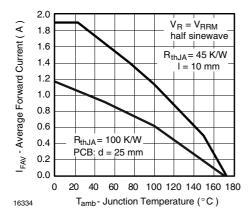


Figure 3. Max. Average Forward Current vs. Ambient Temperature

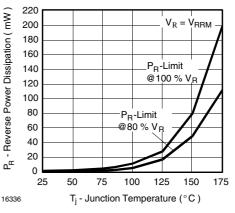


Figure 5. Max. Reverse Power Dissipation vs. Junction Temperature

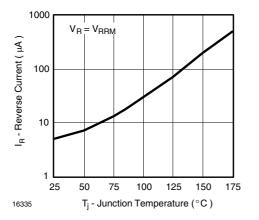


Figure 4. Reverse Current vs. Junction Temperature

## Package Dimensions in mm (Inches)

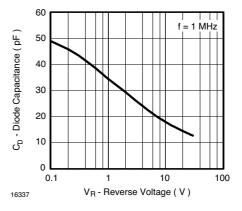
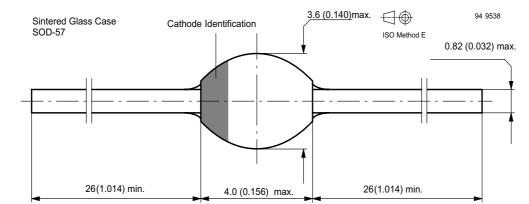


Figure 6. Diode Capacitance vs. Reverse Voltage



## **Vishay Semiconductors**



## **Ozone Depleting Substances Policy Statement**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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